

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
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TYPE : 6PT24B3N3T**

CHIP SIZE	1.29 * 0.94 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	12,384 pcs

Maximum Ratings(Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	30	V
Gate-source voltage	VGSS	±20	V
Drain Current (DC)	ID	4	A

* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	VGSS1	21			V	IG=10uA
2	VGSS2	-21			V	IG=-10uA
3	IGSS1			10	uA	VGS=20V
4	IGSS2			-10	uA	VGS=-20V
5	IDSS			500	nA	VDS=30V VGS=0V
6	BVDSS	32			V	ID=1mA VGS=0V
7	Vth 1	1.2	1.6	2.0	V	ID=250uA
8	Vth 2	1.2	1.5	2.0	V	ID=0.1mA Vds=5V
9	RDS(on)1		25	39	mΩ	ID=2A VGS=10V
10	RDS(on)2		39	58	mΩ	ID=2A VGS=4.5V
11	RDS(on)3		45	68	mΩ	ID=2A VGS=4.0V
12	VSD	0.5		1.1	V	I=100mA VGS=0V
13	Yfs	3			S	VDS=5V ID=2A

※ Built-in ZD between Gate and Source.

NOTE: